James P Mcvittie

List of Publications by Year in descending order

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840776 1199594 16 778 11 12 citations h-index g-index papers 16 16 16 608 docs citations times ranked citing authors all docs

#	Article	IF	CITATIONS
1	Core-Shell Germanium/Germanium–Tin Nanowires Exhibiting Room-Temperature Direct- and Indirect-Gap Photoluminescence. Nano Letters, 2016, 16, 7521-7529.	9.1	54
2	NEM relays using 2-dimensional nanomaterials for low energy contacts., 2013,,.		2
3	Integrating Phase-Change Memory Cell With Ge Nanowire Diode for Crosspoint Memory—Experimental Demonstration and Analysis. IEEE Transactions on Electron Devices, 2008, 55, 2307-2313.	3.0	20
4	Ge-Interface Engineering With Ozone Oxidation for Low Interface-State Density. IEEE Electron Device Letters, 2008, 29, 328-330.	3.9	172
5	Plasma induced wafer charging sensor. Journal of the Chinese Institute of Engineers, Transactions of the Chinese Institute of Engineers, Series A/Chung-kuo Kung Ch'eng Hsuch K'an, 1998, 21, 11-19.	1.1	O
6	Limitations of Plasma Charging Damage Measurements Using MOS Capacitor Structures. Materials Research Society Symposia Proceedings, 1996, 428, 349.	0.1	O
7	lon trajectory distortion and profile tilt by surface charging in plasma etching. Applied Physics Letters, 1994, 64, 1558-1560.	3.3	29
8	Model for oxide damage from gate charging during magnetron etching. Applied Physics Letters, 1993, 62, 1507-1509.	3.3	30
9	Charging damage to gate oxides in an O2magnetron plasma. Journal of Applied Physics, 1992, 72, 4865-4872.	2.5	69
10	Simulation of profile evolution in silicon reactive ion etching with re-emission and surface diffusion. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1992, 10, 1091.	1.6	133
11	The Role of "Antenna―Structure on Thin Oxide Damage from Plasma Induced Wafer Charging. Materials Research Society Symposia Proceedings, 1992, 265, 231.	0.1	O
12	Scaling laws for radio frequency glow discharges for dry etching. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1990, 8, 1654-1662.	2.1	11
13	A tuned Langmuir probe for measurements in rf glow discharges. Journal of Applied Physics, 1990, 67, 6718-6727.	2.5	154
14	A twoâ€dimensional computer simulation for dry etching using Monte Carlo techniques. Journal of Applied Physics, 1989, 65, 1484-1491.	2.5	73
15	Crystalâ€Orientation Dependent Etch Rates and a Trench Model for Dry Etching. Journal of the Electrochemical Society, 1988, 135, 1521-1525.	2.9	27
16	In-Situ Monitoring of Electrical Parameters for Dry Etching. Materials Research Society Symposia Proceedings, 1987, 98, 203.	0.1	4